

Product Overview

FFP08H60S: 8A, 600V, Hyperfast II Diode

For complete documentation, see the data sheet.

The FFP08H60S is a hyperfast II diode and silicon nitride passivated ion-implanted epitaxial planar construction. This device is intended for use as freewheeling/clamping diodes in a variety of switching power supplies and other power switching applications. Its low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

Features

- Hyperfast recovery $T_{rr} = 45\text{ns}$ (@ $I_F = 8\text{A}$)
- Max Forward Voltage, $V_F = 2.1\text{V}$ (@ $T_C = 25^\circ\text{C}$)
- 600V Reverse Voltage and High Reliability
- Avalanche Energy Rated
- RoHS compliant

Applications

- Uninterruptible Power Supply

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Type	$I_{O(\text{rec})}$ Max (A)	t_{rr} Max (ns)	V_{RRM} Max (V)	V_{FM} Max (V)	I_{FSM} Max (A)	I_R Max (mA)	Package Type
FFP08H60STU	0.3744	Pb-free Halide free	Active	Single	8	45	600	2.1	60	0.1	TO-220-2

For more information please contact your local sales support at www.onsemi.com.

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